



FCX591Q

60V PNP MEDIUM POWER TRANSISTOR IN SOT89

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

- BV_{CEO} > -60V
- I_C = -1A High Continuous Collector Current
- I_{CM} = -2A Peak Collector Current
- R_{CE(SAT)} = 295mΩ for a Low Equivalent On-Resistance
- hFE characterized up to 2A for high current gain hold up
- Complementary NPN Type: FCX491
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

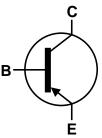
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>@3
- Weight: 0.05 grams (Approximate)

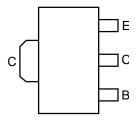




Top View



Device Symbol



Top View Pin Out

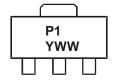
Ordering Information (Notes 4 and 5)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FCX591QTA	P1	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P1 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 7 = 2017) WW = Week code (01 – 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α
Base Current	I _B	-200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		1		
Power Dissipation	(Note 7)	P _D	1.5	W	
	(Note 8)		2.0		
	(Note 6)		125	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ hetaJA}$	83		
	(Note 8)		60		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	22		
Thermal Resistance, Junction to Case (Note 10)		$R_{ heta JC}$	16		
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-65 to +150	°C		

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

 8. Same as Note 6, except the device is mounted on 50mm x 50mm 1oz copper.

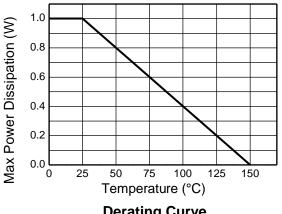
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).

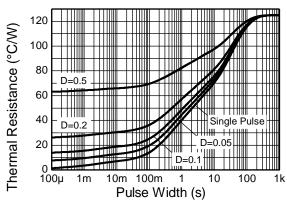
 10. Thermal resistance from junction to the top of the case.

 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



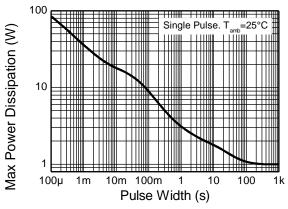
Thermal Characteristics and Derating Information



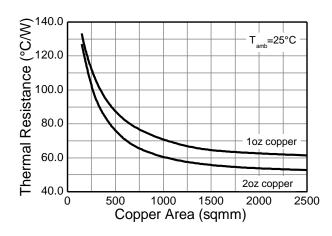


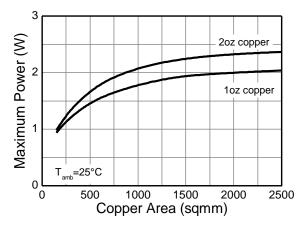
Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation







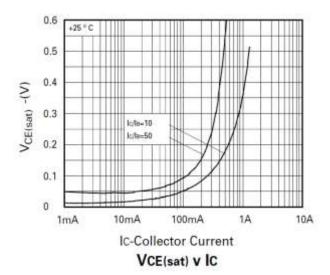
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

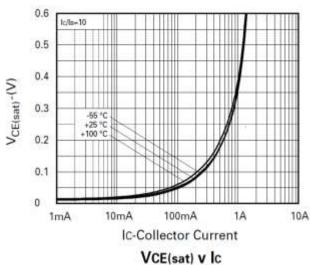
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-80	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-60	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.1	_	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_	<1	-100	nA	V _{CB} = -60V
Emitter Cutoff Current	I _{EBO}	_	<1	-100	nA	$V_{EB} = -5.6V, I_C = 0$
Emitter Cutoff Current	I _{CES}	_	<1	-100	nA	V _{CES} = -60V
DC current transfer Static ratio (Note 12)	h _{FE}	100 100 80 15	220 175 155 40	— 300 —	_	I_{C} = -1mA, V_{CE} = -5V I_{C} = -500mA, V_{CE} = -5V I_{C} = -1A, V_{CE} = -5V I_{C} = -2A, V_{CE} = -5V
Collector-Emitter Saturation Voltage (Note 12)	$V_{\text{CE(sat)}}$	_	-155 -295	-300 -600	mV	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$ $I_C = -1A, I_B = -100 \text{mA}$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	_	-965	-1,200	mV	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Turn-on Voltage (Note 12)	V _{BE(on)}	_	-830	-1,000	mV	I _C = -1A, V _{CE} = -5V
Transitional Frequency	f _T	150	_	_	MHz	$I_E = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
Output capacitance	C_{obo}	_	_	10	pF	V _{CB} = -10V, f = 1MHz,

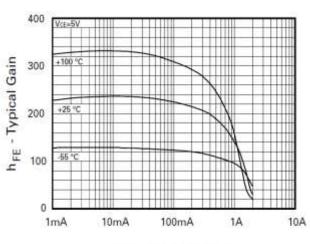
12. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



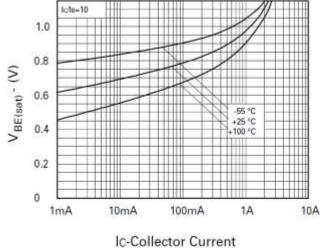
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







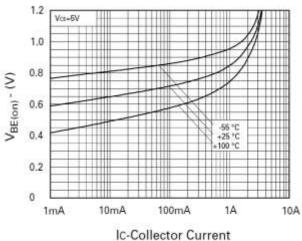
VCE(sat) V IC



Ic-Collector Current

hFE V IC

VBE(sat) v Ic



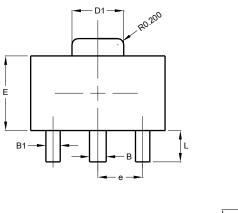
VBE(on) v IC

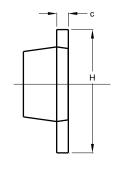


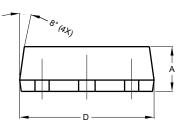
Package Outline Dimensions

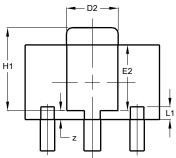
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







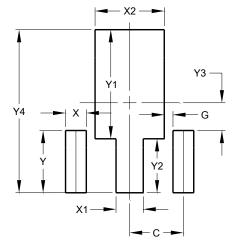


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

January 2018



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